

# Stanford

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## John Lentz

Ph.D. Student in Materials Science and Engineering, admitted Autumn 2016

### Publications

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#### PUBLICATIONS

- **Local ordering in Ge/Ge-Sn semiconductor alloy core/shell nanowires revealed by extended x-ray absorption fine structure (EXAFS)** *APPLIED PHYSICS LETTERS*  
Lentz, J., Woicik, J. C., Bergschneider, M., Davis, R., Mehta, A., Cho, K., McIntyre, P. C.  
2023; 122 (6)
- **Oxide Decomposition and Sn Surface Segregation on Core/Shell Ge/ GeSn Nanowires** *ACS APPLIED ELECTRONIC MATERIALS*  
Braun, M. R., Lentz, J., Bishnoi, I., Meng, A. C., Casalena, L., Cheng, H., McIntyre, P. C.  
2022
- **Bending and precipitate formation mechanisms in epitaxial Ge-core/GeSn-shell nanowires.** *Nanoscale*  
Meng, A. C., Wang, Y., Braun, M. R., Lentz, J. Z., Peng, S., Cheng, H., Marshall, A. F., Cai, W., McIntyre, P. C.  
2021
- **Growth mode control for direct-gap core/shell Ge/GeSn nanowire light emission** *MATERIALS TODAY*  
Meng, A. C., Braun, M. R., Wang, Y., Peng, S., Tan, W., Lentz, J., Xue, M., Pakzad, A., Marshall, A. F., Harris, J. S., Cai, W., McIntyre, P. C.  
2020; 40: 101–13